

CLAIMS

etching method comprising etching a metal  
a copper, silver, gold, or an alloy of  
ment at least one of these metals by  
containing at least nitrogen oxide  
the plasma.

etching method as claimed in Claim 1  
is a mixed gas of nitrogen oxide and  
containing hydrogen.

etching method as claimed in Claim 2  
containing hydrogen is one or two or more  
group consisting of ammonia, a hydrocarbon  
containing hydrocarbon, and hydrogen.

etching method as claimed in one of  
a mask material covering the metal  
one selected from the group consisting of  
alloy, aluminum, and an aluminum alloy.

1. A dry etching method comprising etching a metallic surface selected from copper, silver, gold, or an alloy containing as a main component at least one of these metals by plasma of an etching gas containing at least nitrogen oxide while being reacted with the plasma.
2. A dry etching method as claimed in Claim 1, wherein the etching gas is a mixed gas of nitrogen oxide and hydrogen, or a compound containing hydrogen.
3. A dry etching method as claimed in Claim 2, wherein the compound containing hydrogen is one or two or more selected from the group consisting of ammonia, a hydrocarbon, a halogen-containing hydrocarbon, and hydrogen sulfide.
4. A dry etching method as claimed in one of Claims 1 to 3, wherein a mask material covering the metallic surface on etching is one selected from the group consisting of titanium, a titanium alloy, aluminum, and an aluminum alloy.

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